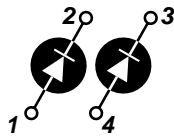
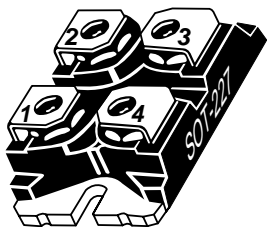


Anti-Parallel
APT2X30S20J



Parallel
APT2X31S20J



APT2X31S20J 200V 45A
APT2X30S20J 200V 45A

DUAL DIE ISOTOP® PACKAGE HIGH VOLTAGE SCHOTTKY DIODES

PRODUCT APPLICATIONS	PRODUCT FEATURES	PRODUCT BENEFITS
<ul style="list-style-type: none"> • Parallel Diode <ul style="list-style-type: none"> -Switchmode Power Supply -Inverters • Free Wheeling Diode <ul style="list-style-type: none"> -Motor Controllers -Converters • Snubber Diode • Uninterruptible Power Supply (UPS) • 48 Volt Output Rectifiers • High Speed Rectifiers 	<ul style="list-style-type: none"> • Ultrafast Recovery Times • Soft Recovery Characteristics • Popular SOT-227 Package • Low Forward Voltage • High Blocking Voltage • Low Leakage Current 	<ul style="list-style-type: none"> • Low Losses • Low Noise Switching • Cooler Operation • Higher Reliability Systems • Increased System Power Density

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT2X31_30S20J	UNIT
V_R	Maximum D.C. Reverse Voltage	200	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_F(AV)$	Maximum Average Forward Current ($T_C = 105^\circ\text{C}$, Duty Cycle = 0.5)	45	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	81	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	320	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AVL}	Avalanche Energy (2A, 15mH)	30	mJ

STATIC ELECTRICAL CHARACTERISTICS

Symbol		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 30\text{A}$.80	.85	Volts
		$I_F = 60\text{A}$.91		
		$I_F = 30\text{A}, T_J = 125^\circ\text{C}$.67		
I_{RM}	Maximum Reverse Leakage Current	$V_R = V_R \text{ Rated}$		0.5	mA
		$V_R = V_R \text{ Rated}, T_J = 125^\circ\text{C}$		15	
C_T	Junction Capacitance, $V_R = 200\text{V}$		149		pF

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s$ $V_R = 133V, T_C = 25^\circ C$	-	55		ns
Q_{rr}	Reverse Recovery Charge		-	188		nC
I_{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s$ $V_R = 133V, T_C = 125^\circ C$	-	97		ns
Q_{rr}	Reverse Recovery Charge		-	448		nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Charge	$I_F = 30A, di_F/dt = -700A/\mu s$ $V_R = 133V, T_C = 125^\circ C$	-	66		ns
Q_{rr}	Reverse Recovery Charge		-	963		nC
I_{RRM}	Maximum Reverse Recovery Current		-	24		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.04	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			20	
W_T	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Terminal & Mounting Torque			10	lb•in
				1.1	N•m

APT Reserves the right to change, without notice, the specifications and information contained herein.

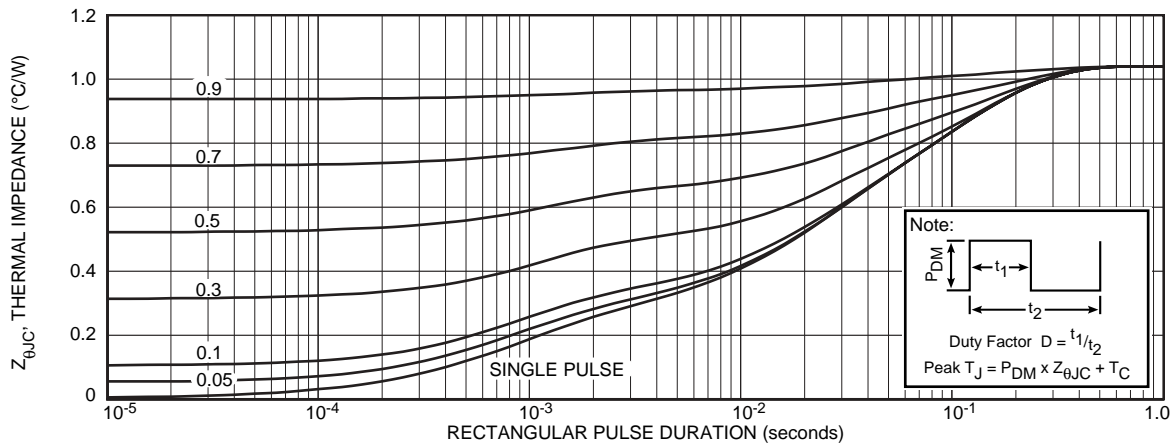


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

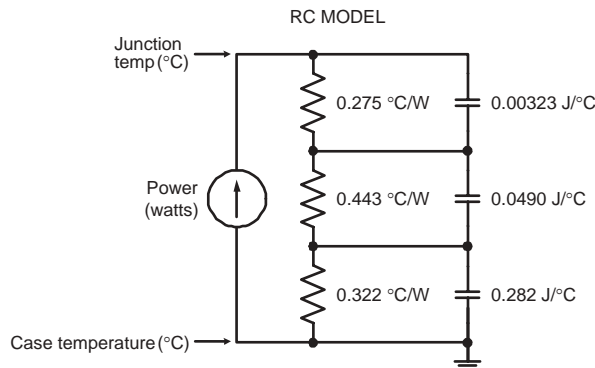


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

APT2X31_30S20J

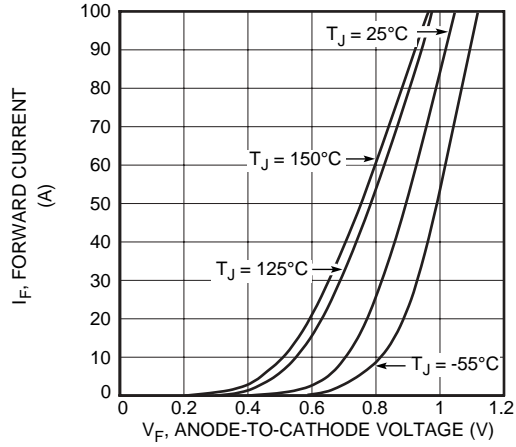


Figure 2. Forward Current vs. Forward Voltage

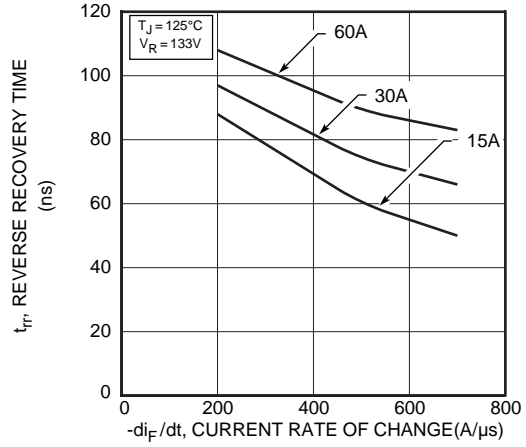


Figure 3. Reverse Recovery Time vs. Current Rate of Change

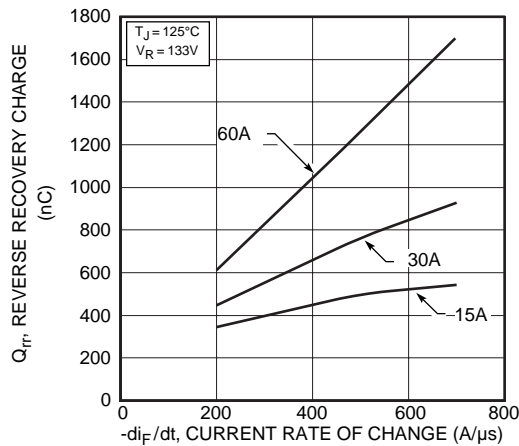


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

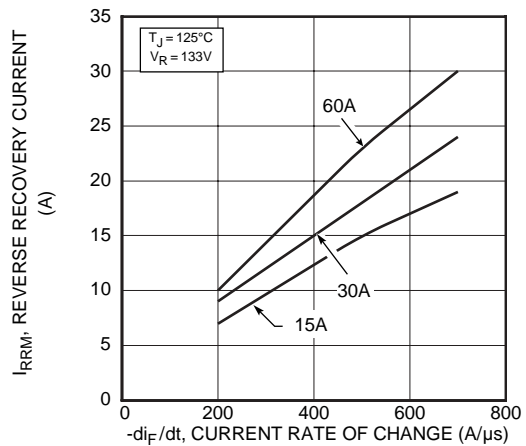


Figure 5. Reverse Recovery Current vs. Current Rate of Change

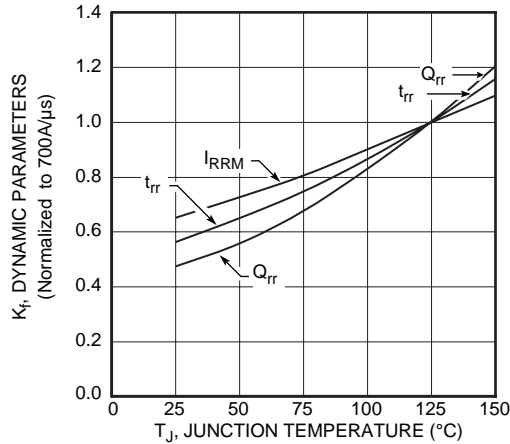


Figure 6. Dynamic Parameters vs. Junction Temperature

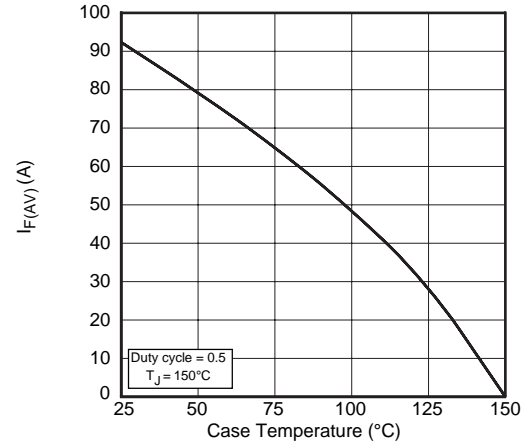


Figure 7. Maximum Average Forward Current vs. Case Temperature

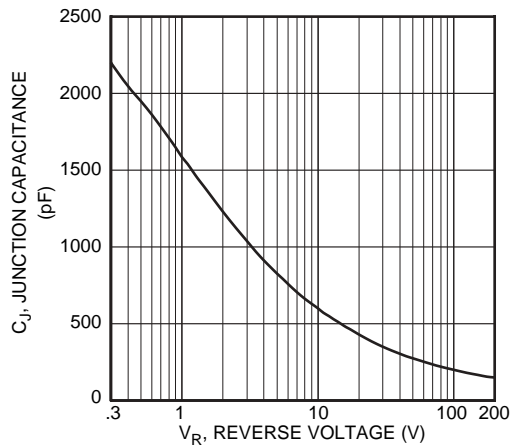


Figure 8. Junction Capacitance vs. Reverse Voltage

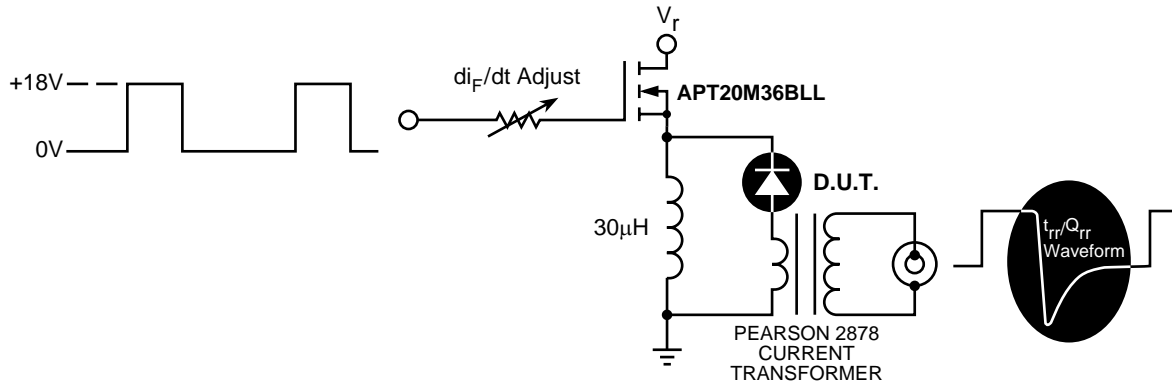


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

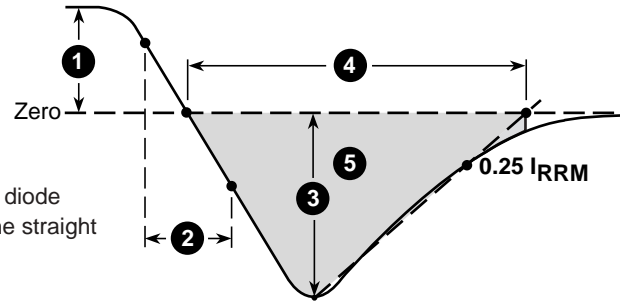
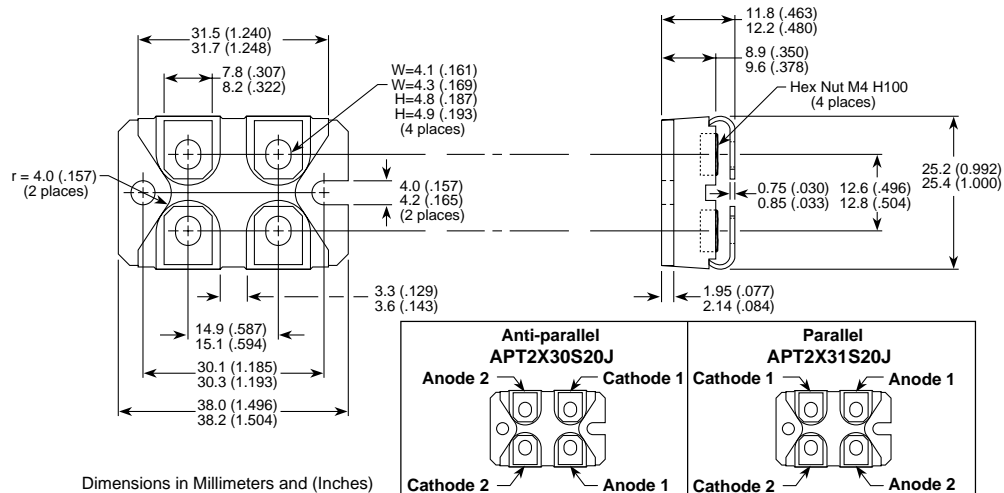


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 Package Outline



Dimensions in Millimeters and (Inches)

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[MT18HTF12872PZ-667G1](#) [MT18HTF25672FDZ-667H1D6](#) [MT18HTF25672PZ-80EH1](#) [MT18RTF25672FDZ-667H1D6](#)
[MT36HTF51272FZ-667H1D4](#) [MT36HTF51272FZ-667H1D6](#) [MT8HTF12864HTZ-667H1](#) [MT9HTF6472PZ-667G1](#) [MT9HVF12872PZ-](#)
[80EH1](#) [MT9HVF6472PZ-667G1](#) [ND104N16K](#) [25.163.0653.1](#) [25.163.2453.0](#) [25.163.4253.0](#) [25.190.2053.0](#) [25.194.3453.0](#) [25.320.4853.1](#)
[25.320.5253.1](#) [25.325.3653.1](#) [25.326.3253.1](#) [25.326.3553.1](#) [25.330.1653.1](#) [25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#)